Table 25-15. XA1 and XA0 Coding

XA1	XA0	Action when XTAL1 is Pulsed
0	0	Load Flash or EEPROM Address (High or low address byte determined by BS1).
0	1	Load Data (High or Low data byte for Flash determined by BS1).
1	0	Load Command
1	1	No Action, Idle

Table 25-16. Command Byte Bit Coding

Command Byte	Command Executed
1000 0000	Chip Erase
0100 0000	Write Fuse bits
0010 0000	Write Lock bits
0001 0000	Write Flash
0001 0001	Write EEPROM
0000 1000	Read Signature Bytes and Calibration byte
0000 0100	Read Fuse and Lock bits
0000 0010	Read Flash
0000 0011	Read EEPROM

25.7 Parallel Programming

25.7.1 Enter Programming Mode

The following algorithm puts the device in Parallel (High-voltage) Programming mode:

1. Set Prog_enable pins listed in Table 25-14 on page 300 to “0000”, RESET pin to 0V and V_{CC} to 0V.
2. Apply 4.5 - 5.5V between V_{CC} and GND.

Ensure that V_{CC} reaches at least 1.8V within the next 20 µs.

3. Wait 20 - 60 µs, and apply 11.5 - 12.5V to RESET.
4. Keep the Prog_enable pins unchanged for at least 10µs after the High-voltage has been applied to ensure the Prog_enable Signature has been latched.
5. Wait at least 300 µs before giving any parallel programming commands.
6. Exit Programming mode by power the device down or by bringing RESET pin to 0V.

If the rise time of the V_{CC} is unable to fulfill the requirements listed above, the following alternative algorithm can be used.

1. Set Prog_enable pins listed in Table 25-14 on page 300 to “0000”, RESET pin to 0V and V_{CC} to 0V.
2. Apply 4.5 - 5.5V between V_{CC} and GND.
3. Monitor V_{CC}, and as soon as V_{CC} reaches 0.9 - 1.1V, apply 11.5 - 12.5V to RESET.